```
(FILE 'USPAT' ENTERED AT 16:03:47 ON 20 DEC 94)
 L1
          391449 S COMPRESS?
           24226 S L1 AND MEMORY
 L2
           21219 S ONE (W) BIT
 L3
 L4
             457 S L1(P)L3
             360 S L4 AND L2
 L5
               8 S L5 AND 365/CLAS
 L6
          921782 S READ?
 L7
           34937 S L1(P)L7
 L8
 L9
              93 S L8 AND 365/CLAS
 L10
              3 S L9 AND 365/201/CCLS
              11 S L9 AND WIRED
 L11
 => d l10 1-3
 1. 5,313,424, May 17, 1994, Module level electronic_redundancy; Robert
 D. Adams, et al., **365/200**, **96**, **201**, **210** [IMAGE AVAILABLE]
 2 5,148,398, Sep. 15, 1992, Semiconductor memory device with built-in
 test circuit and method for testing the same; Tohru Kohno, (**365/201***;
 371/21.1 [IMAGE AVAILABLE]
3 4,918,378, Apr. 17, 1990, Method and circuitry for enabling internal
 test operations in a VLSI chip; Haluk Katircioglu, et al., **365/201**;
 371/21.2, 22.4, 22.5 [IMAGE AVAILABLE]
 => d 16 1-8
 1. 5,357,475, Oct. 18, 1994, Method for detaching sectors in a flash
 EEPROM **memory** array; Robert N. Hasbun, et al., **365/218**, **200**;
 371/10.1, 10.2, 11.1, 21.1; 395/575 [IMAGE AVAILABLE]
    5,341,339, Aug. 23, 1994, Method for wear leveling in a flash EEPROM
 **memory**; Steven E. Wells, **365/218**, **185**, **900** [IMAGE
 AVAILABLE]
 31 5,337,275, Aug. 9, 1994, Method for releasing space in flash EEPROM
 */*memory** array to allow the storage of **compressed** data; Richard P.
 Garner, **365/189.01**, **230.01**, **900** [IMAGE AVAILABLE]
```